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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	Unknown 10/790,510
Filing Date	Even Date Herewith 3/01/2004
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown 2823
Examiner Name	Unknown W. DAVID COLEMAN

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Attorney Docket No: 303.689US2

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**INFORMATION DISCLOSURE
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Application Number	Unknown <u>10/790,570</u>
Filing Date	Even Date Herewith <u>3/01/2004</u>
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown <u>2823</u>
Examiner Name	Unknown <u>W. DAVID COLEMAN</u>

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Attorney Docket No: 303.689US2

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Group Art Unit	Unknown 2823
Examiner Name	Unknown W. DAVID COLEMAN

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